NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRAL2023-6** is a Common Base Device Designed for class C Amplifier Applications in L-Band FM Microwave Links.

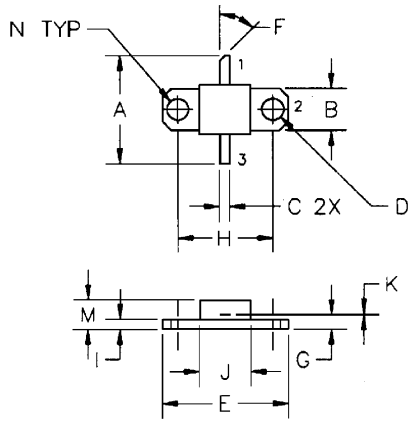
FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	1.25 A
V_{CES}	40 V
P_{DISS}	21 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	8.0 °C/W

PACKAGE STYLE .250 2L FLG (C)



1 = COLLECTOR 2 = BASE
3 = EMITTER

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 50 mA	40			V
BV_{EBO}	I_E = 1.0 mA	3.5			V
I_{CBO}	V_{CB} = 22 V			1.25	mA
h_{FE}	V_{CE} = 5.0 V I_C = 500 mA	10		90	---
C_{OB}	V_{CB} = 22 V f = 1.0 MHz			10	pF
P_G	V_{CE} = 22 V P_{OUT} = 6.0 W f = 2000 to 2300 MHz	6.8			dB
η_C		40			%